

SANYO

No.5183

2SA1968

NPN Triple Diffused Planar Silicon Transistor
**High-Voltage Amp,
 High-Voltage Switching Applications**

Features

- High breakdown voltage ($V_{CEO \text{ min}} = -900\text{V}$).
- Small Cob (Cob typ = 2.2pF).
- High reliability (Adoption of HVP process).
- Package of full isolation type.

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

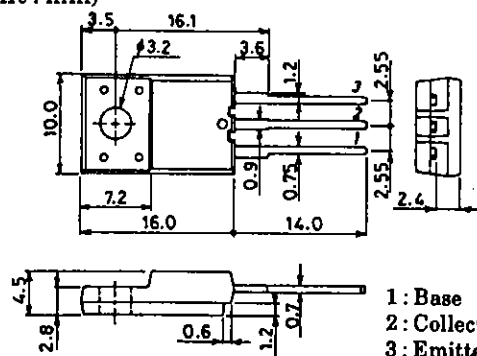
			unit
Collector-to-Base Voltage	V_{CBO}	-900	V
Collector-to-Emitter Voltage	V_{CEO}	-900	V
Emitter-to-Base Voltage	V_{EBO}	-7	V
Collector Current	I_C	-10	mA
Collector Current (Pulse)	I_{CP}	-30	mA
Collector Dissipation	P_C	2	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = -900\text{V}, I_E = 0$			-1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			-1	μA
DC Current Gain	h_{FE}	$V_{CE} = -5\text{V}, I_C = -1\text{mA}$	20		50	
Gain-Bandwidth Product	f_T	$V_{CE} = -10\text{V}, I_C = -1\text{mA}$		6		MHz
Output Capacitance	Cob	$V_{CB} = -100\text{V}, f = 1\text{MHz}$		2.2		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = -500\mu\text{A}, I_B = -100\mu\text{A}$			-1	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = -500\mu\text{A}, I_B = -100\mu\text{A}$			-1.5	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-900			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, R_{BE} = \infty$	-900			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-7			V

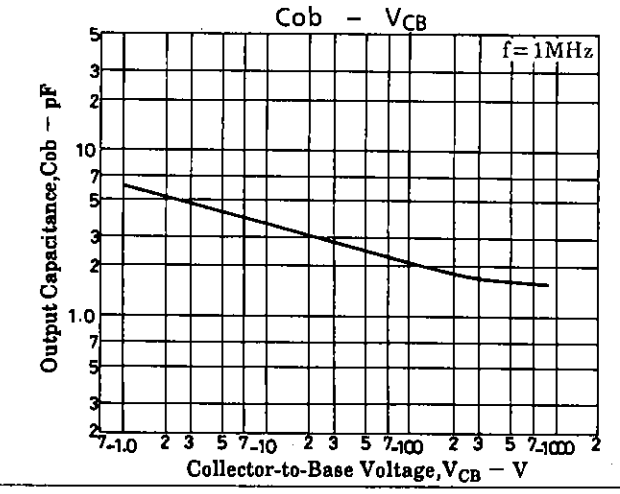
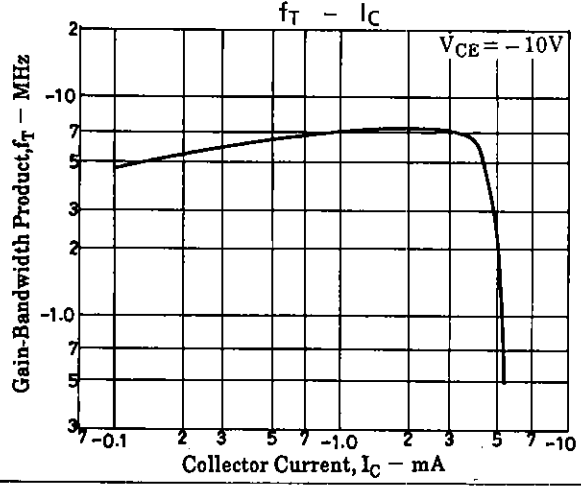
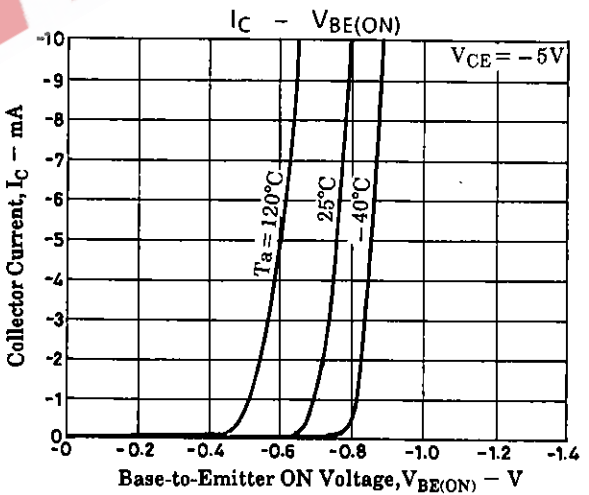
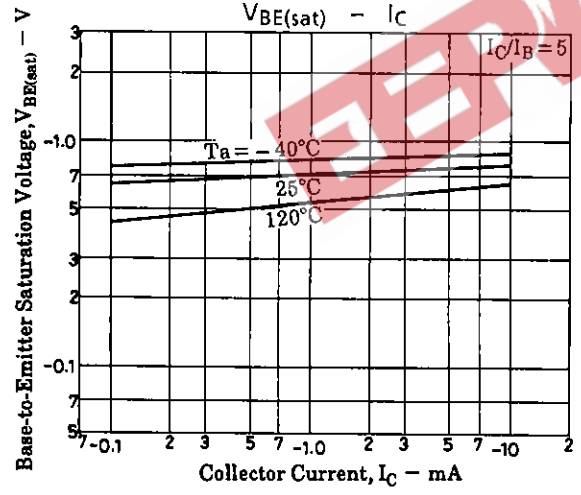
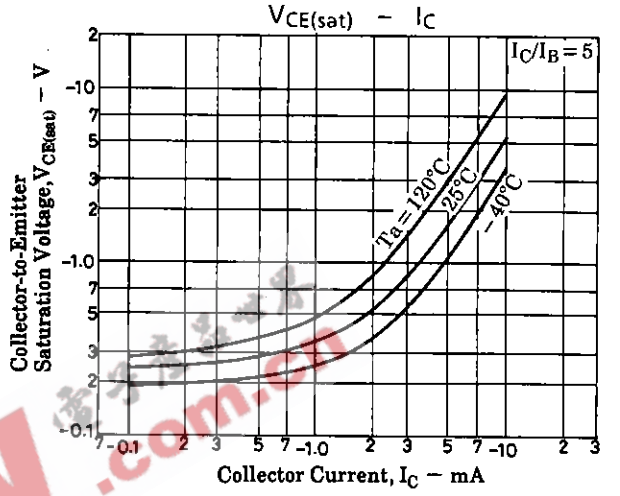
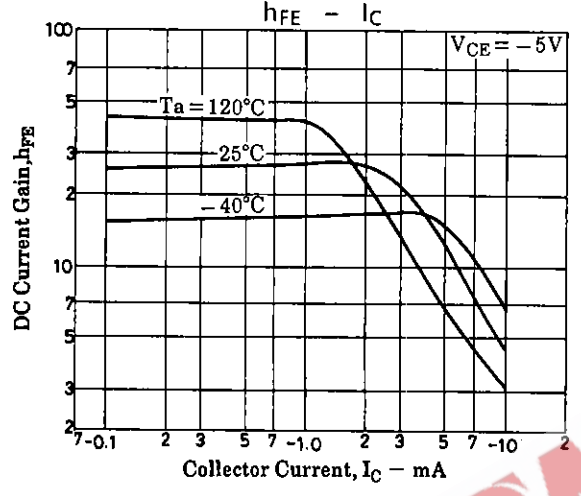
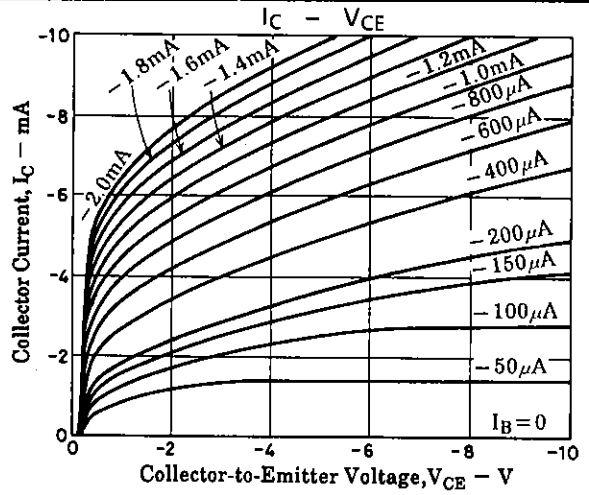
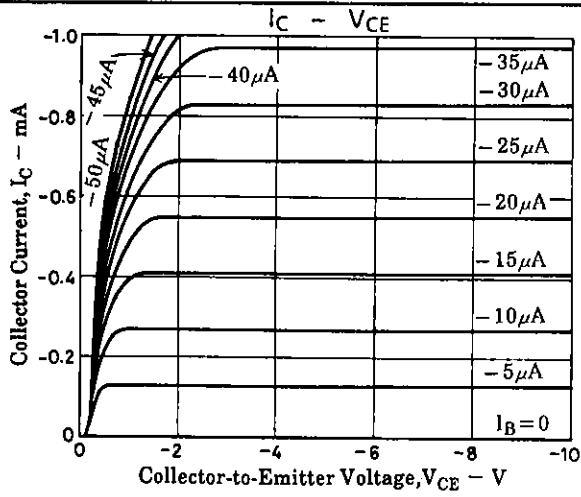
Package Dimensions 2079B

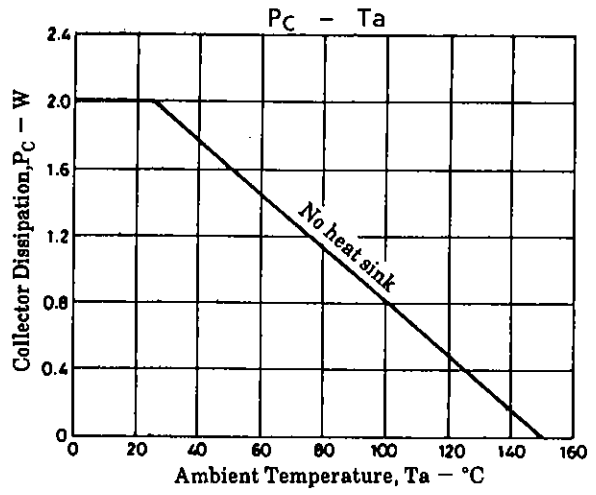
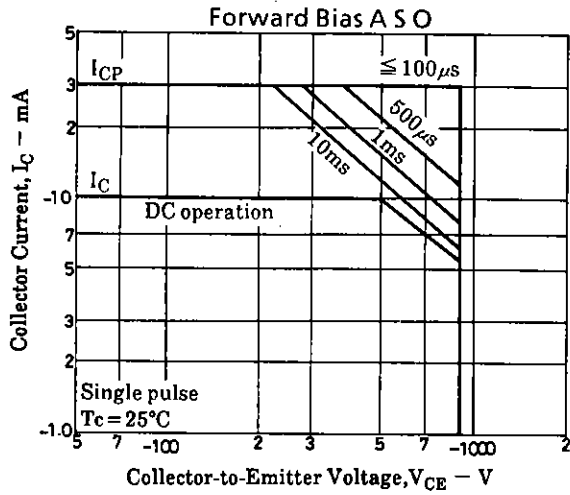
(unit : mm)



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